

IN THE CLAIMS

Please cancel claims 1, 3, 4 and 7, and amend claims 2, 5, 6, 10 and 13 as follows:

1. (CANCELED)

2. (CURRENTLY AMENDED) An integrated RF filter for use at microwave frequencies comprising:

first and second capacitors connected in series between an input and an output of said filter;
an inductor, connected between said input and said output of said filter, in parallel to said series connected capacitors, said first and second capacitors and said inductor comprising a tank circuit; and

a shunt resistor connected between ground, and the common side of said first and second capacitors;

each of said inductor, capacitors and resistor being a low-Q integrated element, yet wherein said integrated RF filter circuit results in a high-Q passive filter at microwave frequencies; and

wherein the value of said shunt resistor is selected to be equal in magnitude to the impedance of said inductor and capacitor tank circuit at its resonant frequency.

3. (CANCELED)

4. (CANCELED)

5. (CURRENTLY AMENDED) The integrated RF filter of claim [[3]] 2, implemented in a silicon technology.

6. (CURRENTLY AMENDED) The integrated RF filter of claim [[3]] 5, wherein said silicon technology comprises silicon bipolar technology.

7. (CANCELED)

8. (ORIGINAL) The integrated RF filter of claim 5, wherein said capacitors are implemented as variable capacitors, thereby permitting a degree of tuning of the filter frequency of the circuit during use.

9. (ORIGINAL) The integrated RF filter of claim 8 wherein said variable capacitors are implemented using varactor diodes.

10. (CURRENTLY AMENDED) The integrated RF filter of claim 5, wherein ~~said the~~ centre of ~~said the~~ operating frequency band of said integrated RF filter exceeds 800 MHz.

13. (CURRENTLY AMENDED) The integrated RF filter of claim ~~[[3]]~~ 2, wherein the values of each of said inductor, capacitors and resistor are selected to provide a narrow band notch filter.